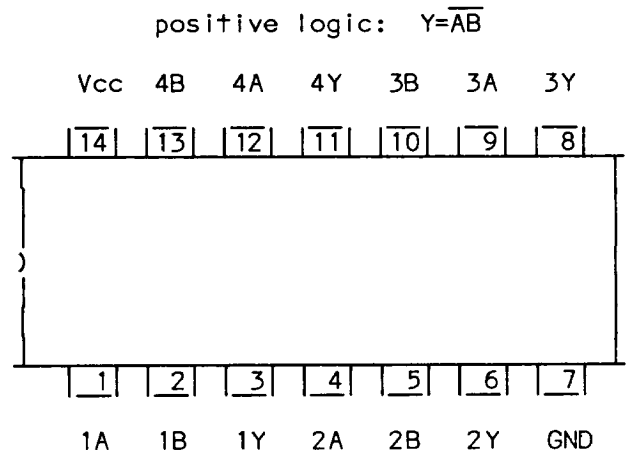


ADVANCED LOW-POWER
SCHOTTKY TTL

TYPES SN54ALS903 and SN74ALS903
QUAD 2-INPUT NAND BUFFERS with OPEN COLLECTOR OUTPUTS

- * QUAD 2-INPUT NAND BUFFERS w/O.C. OUTPUTS
- * ADVANCED OXIDE-ISOLATED, ION-IMPLANTED SCHOTTKY TTL PROCESS
- * FUNCTIONALLY and PIN-for-PIN COMPATIBLE with TTL COUNTERPART
- * IMPROVED AC PERFORMANCE over LS COUNTERPART
- * HALF the POWER of LS COUNTERPART
- * IMPROVED INPUT THRESHOLD VOLTAGE
- * IMPROVED LINE RECEIVING CHARACTERISTICS

ELECTRICAL PINOUT



This advanced low-power Schottky device has been fabricated by an advanced oxide-isolated, ion-implanted Schottky TTL process developed by TI. The major benefit of this process is the improvement of the speed-power product by the reduction of parasitic and side-wall capacitance and enhanced f_T . The ALS family features the same output drive characteristics as the LS family.

switching characteristics $V_{cc}=5V, T_a=25^\circ C, C_l=50pF, R_l=667ohms$

PARAMETER	SN54ALS903		SN74ALS903		UNIT
	min	typ max	min	typ max	
t_{plh} Propagation delay time, low-to-high-level output	14.5		14.5		ns
t_{phl} Propagation delay time, high-to-low-level output	10.0		10.0		ns

supply current over recommended operating free-air temperature range

PARAMETER	TEST CONDITIONS	SN54ALS903		SN74ALS903		UNIT
		typ	max	typ	max	
I_{cch} Supply current, outputs high	$V_{cc}=MAX, V_i=0V$.86	2.1	.86	2.1	mA
I_{ccl} Supply current, outputs low	$V_{cc}=MAX, V_i=4.5V$	4.0	6.8	4.0	6.8	mA

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